N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a, e]	Q_g (Typ)
30	0.0029 at V_{GS} = 10 V	90	82 nC
	0.0033 at V_{GS} = 4.5 V	90	

FEATURES

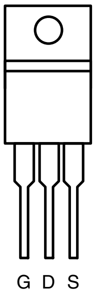
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU

RoHS
COMPLIANT

APPLICATIONS

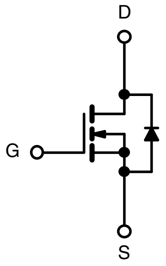
- OR-ing
- Server
- DC/DC

TO-220AB



Top View

DRAIN connected to TAB



N-Channel MOSFET

Ordering Information: SUP90N03-03-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	90[a, e]	A
	T_C = 70 °C		90[e]	
	T_A = 25 °C		28.8[b, c]	
	T_A = 70 °C		27[b, c]	
Pulsed Drain Current		I_{DM}	90	
Avalanche Current Pulse	L = 0.1 mH	I_{AS}	36	
Single Pulse Avalanche Energy		E_{AS}	64.8	V
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	90[a, e]	A
	T_A = 25 °C		3.13[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	250[a]	W
	T_C = 70 °C		175	
	T_A = 25 °C		3.75[b, c]	
	T_A = 70 °C		2.63[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 sec	R_{thJA}	32	40	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	0.5	0.6	

Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 sec.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

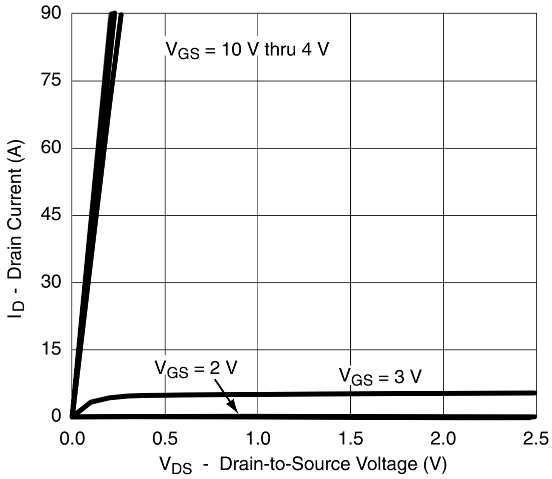
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.5		2.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	90			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 28.8 A		0.0024	0.0029	Ω
		V_{GS} = 4.5 V, I_D = 27 A		0.0027	0.0033	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 28.8 A		160		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		12065		pF
Output Capacitance	C_{oss}			1725		
Reverse Transfer Capacitance	C_{rss}			970		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 28.8 A		171	257	nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 28.8 A		81.5	123	
Gate-Source Charge	Q_{gs}			34		
Gate-Drain Charge	Q_{gd}			29		
Gate Resistance	R_g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.625 Ω $I_D \cong$ 24 A, V_{GEN} = 10 V, R_g = 1 Ω		18	27	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			70	105	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.67 Ω $I_D \cong$ 22.5 A, V_{GEN} = 4.5 V, R_g = 1 Ω		55	83	
Rise Time	t_r			180	270	
Turn-Off Delay Time	$t_{d(off)}$			55	83	
Fall Time	t_f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			90	A
Pulse Diode Forward Current[a]	I_{SM}				90	
Body Diode Voltage	V_{SD}	I_S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20 A, di/dt = 100 A/µs, T_J = 25 °C		52	78	ns
Body Diode Reverse Recovery Charge	Q_{rr}			70.2	105	nC
Reverse Recovery Fall Time	t_a			27		ns
Reverse Recovery Rise Time	t_b			25		

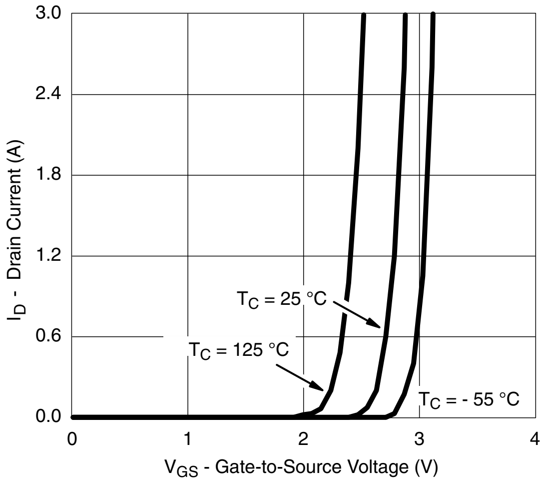
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

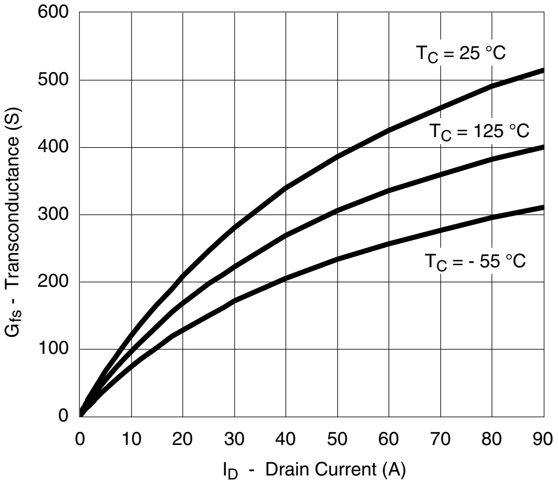
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



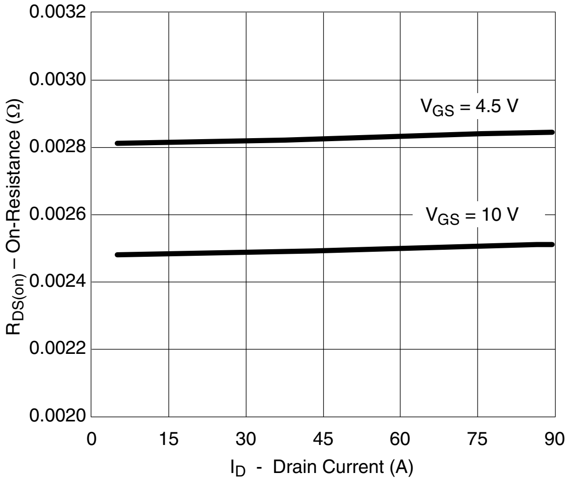
Output Characteristics



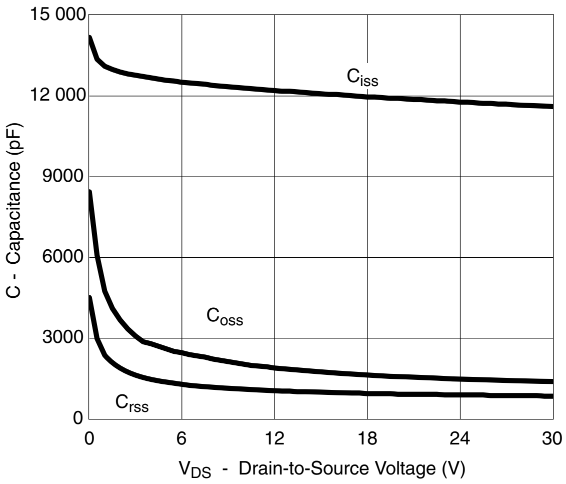
Transfer Characteristics



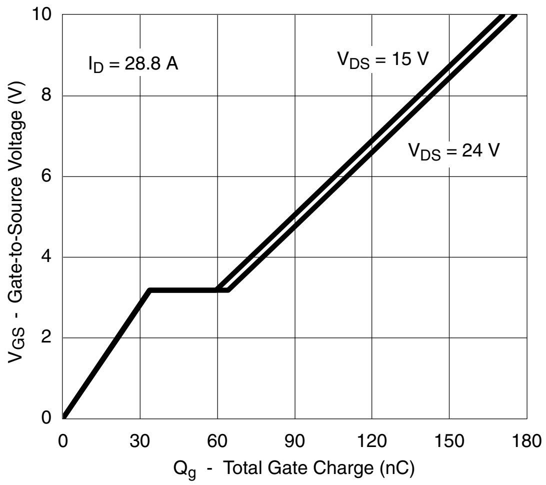
Transconductance



$R_{DS(on)}$ vs. Drain Current

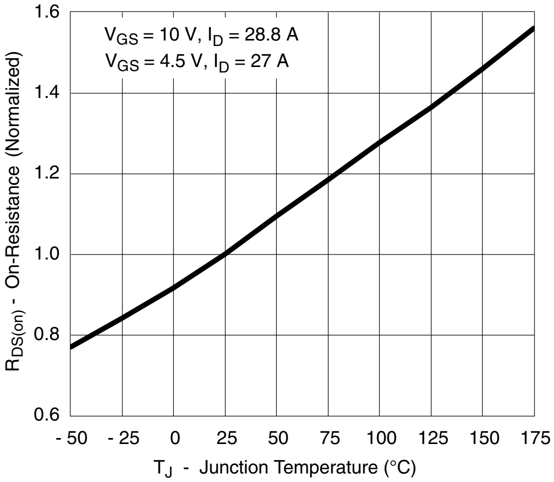


Capacitance

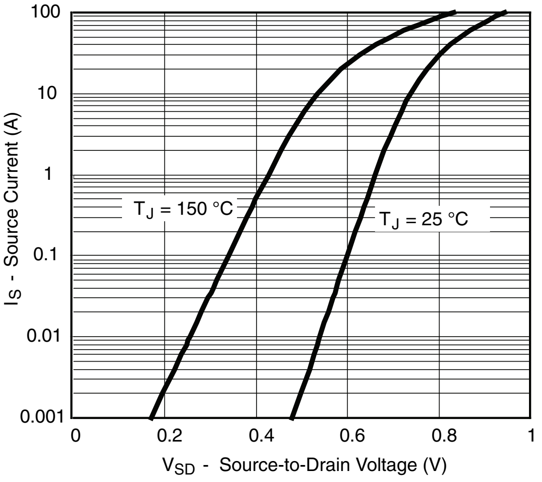


Gate Charge

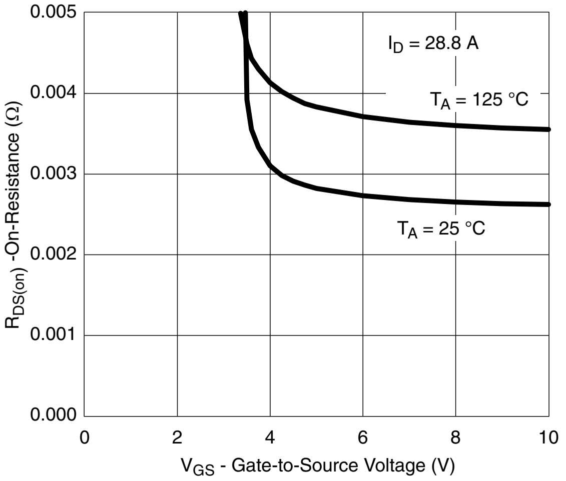
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



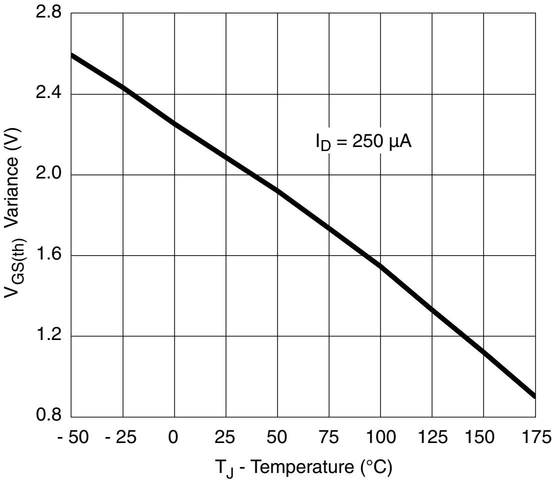
On-Resistance vs. Junction Temperature



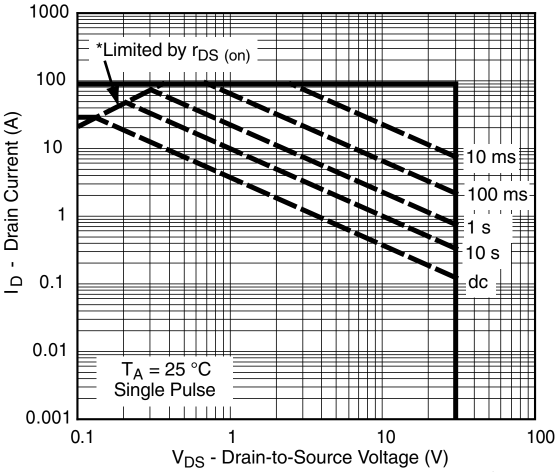
Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature



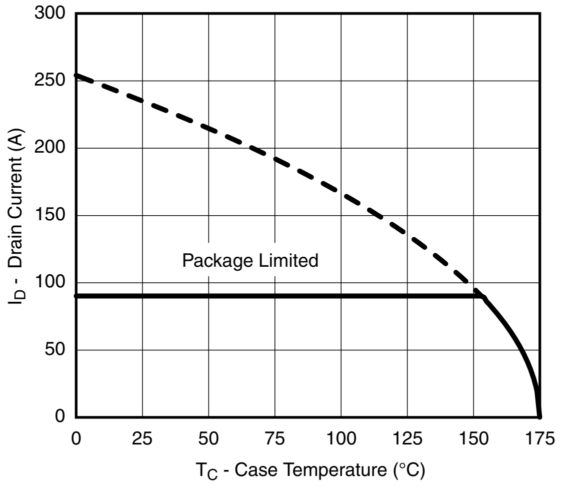
Threshold Voltage



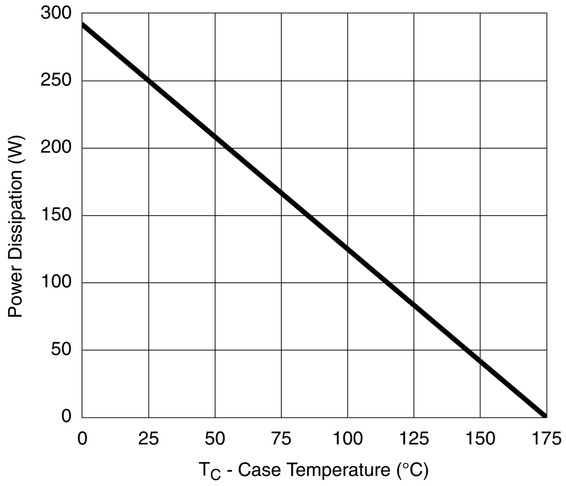
*V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

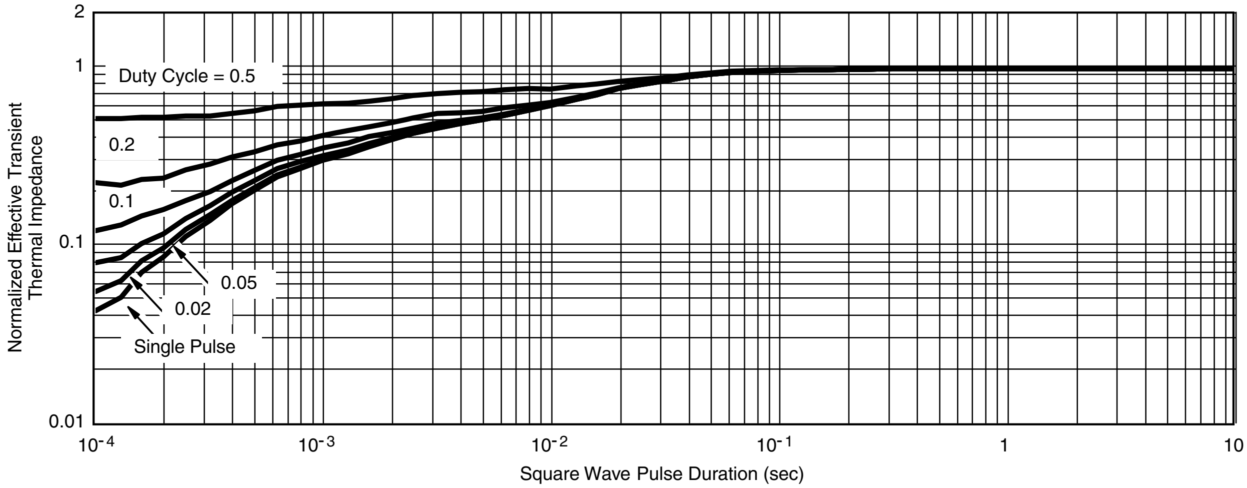


Current Derating*



Power Derating

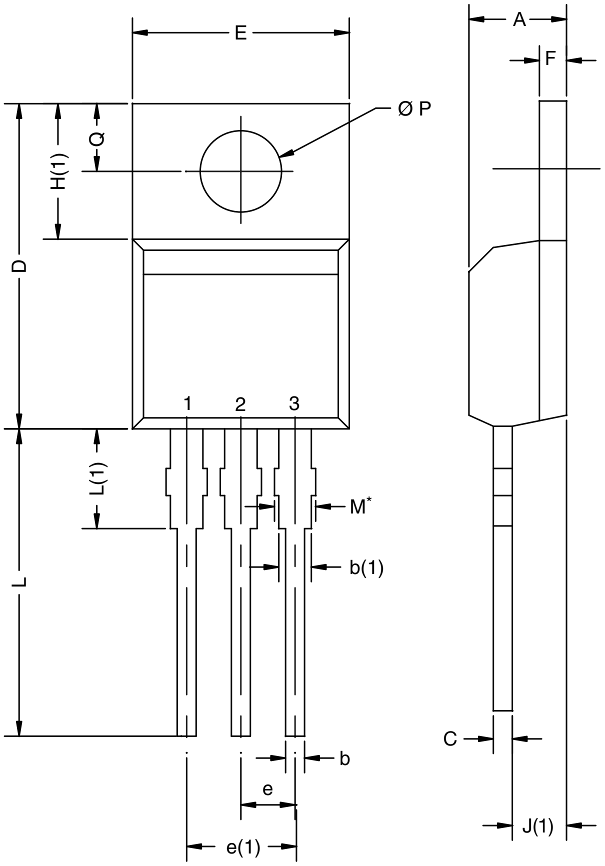
*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?74341

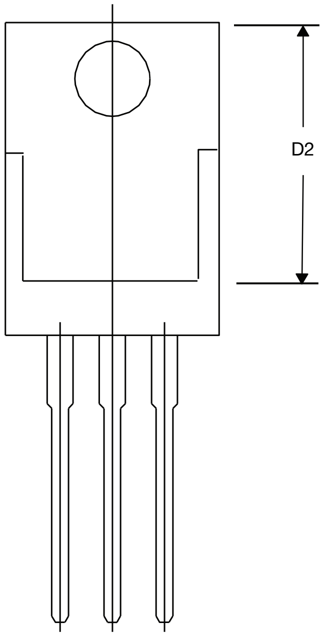
TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.